

Decoherence and Materials in Josephson Qubits

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Matthias Steffen, Kristine Lang, Dave Pappas, Sae Woo Nam
NIST Boulder



National Institute of Standards and Technology • Technology Administration • U.S. Department of Commerce

ARDA



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We know *experimentally* **very little**

- little Rabi data / low coherence
- eventually need ~99.99% fidelity

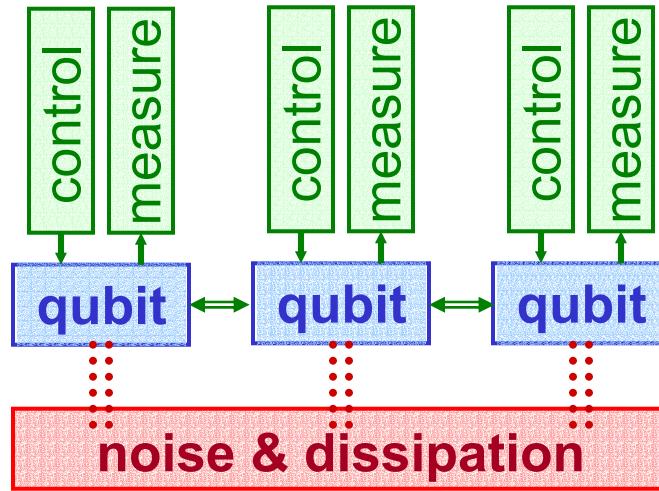
First-study of issues with Josephson qubits



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Challenge: Coupling vs. Decoherence



Experimental challenge:
Couple qubits to each other,
control, & measure,
not noise and dissipation

Experimental Systems

Atoms

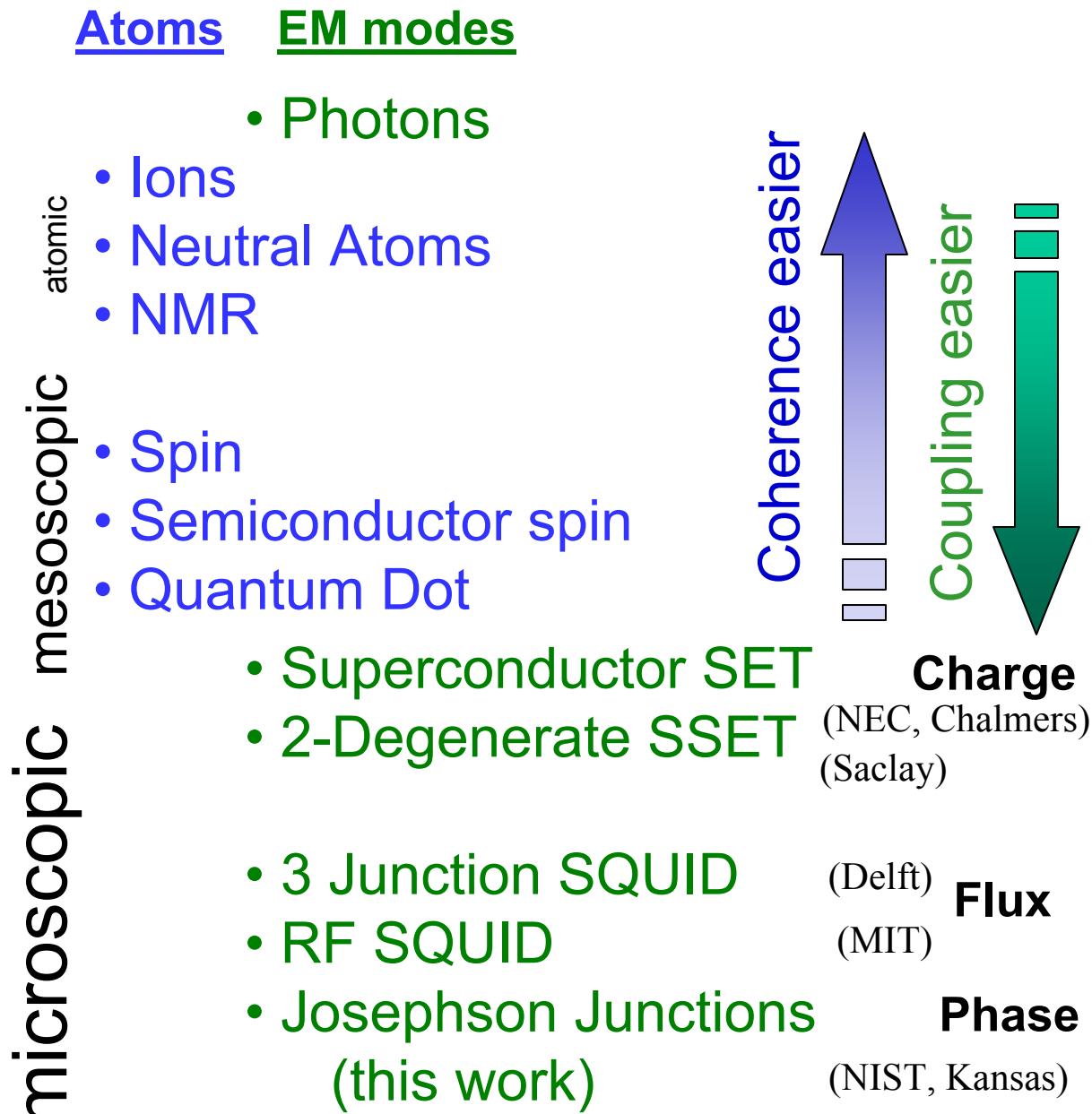
Feynmann (1985):
“it seems that the laws of physics present no barrier to reducing the size of computers until bits are the size of atoms, and quantum behavior holds sway.”

- atomic
 - Ions
 - Neutral Atoms
 - NMR

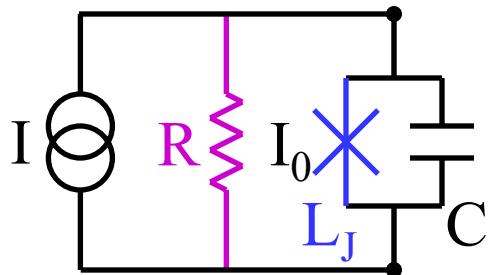
- mesoscopic
 - Spin
 - Semiconductor spin
 - Quantum Dot

Experimental Systems

Feynmann (1985):
“it seems that the laws of physics present no barrier to reducing the size of computers until bits are the size of atoms, and quantum behavior holds sway.”



Qubit: Nonlinear LC resonator



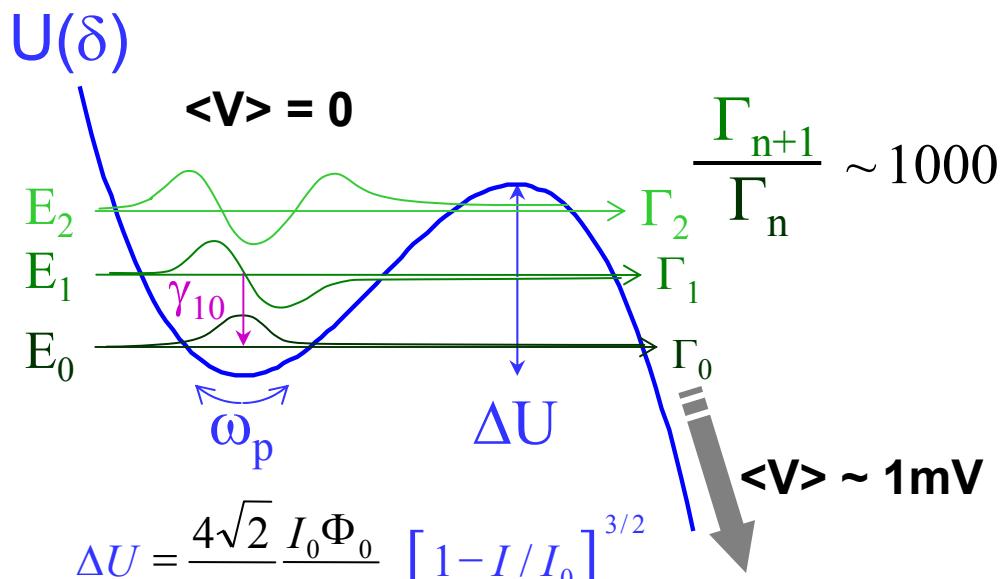
$$I = I_0 \sin \delta$$

$$V = \frac{\Phi_0}{2\pi} \dot{\delta}$$

$$\dot{I}_j = I_0 \cos \delta \quad \dot{\delta} \\ \equiv (1/L_J)V$$

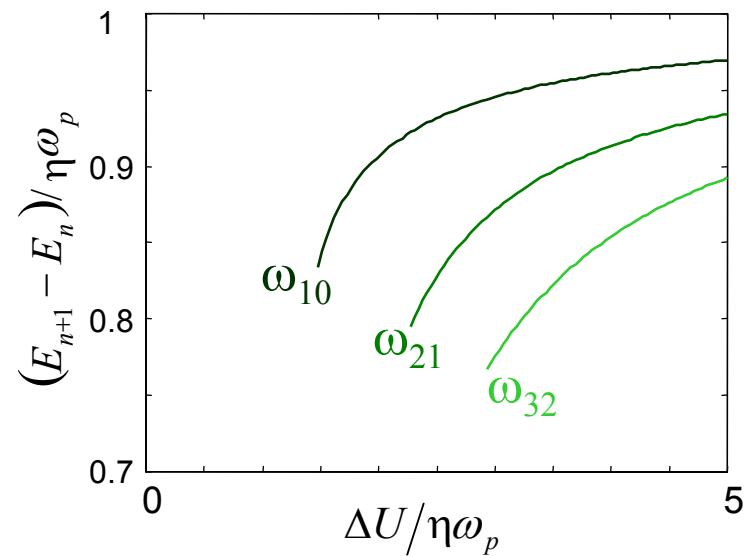
$$L_J = \Phi_0 / 2\pi I_0 \cos \delta$$

nonlinear inductor



$$\omega_p = \left(\frac{2\sqrt{2}\pi}{\Phi_0} \frac{I_0}{C} \right)^{1/2} \left[1 - I/I_0 \right]^{1/4}$$

$\gamma_{10} \approx 1/RC$ Lifetime of state $|1\rangle$



Josephson-Junction Qubit

- State Preparation

Wait $t > 1/\gamma_{10}$ for decay to $|0\rangle$

- Qubit logic with bias control

$$I = I_{dc} + \delta I_{dc}(t) + I_{\mu wc}(t) \cos \omega_{10} t + I_{\mu ws}(t) \sin \omega_{10} t$$

$$\begin{aligned} H_{(2)} = & \sigma_x \bullet I_{\mu wc} \bullet (\eta / 2\omega_{10} C)^{1/2} / 2 \\ & + \sigma_y \bullet I_{\mu ws} \bullet (\eta / 2\omega_{10} C)^{1/2} / 2 \\ & + \sigma_z \bullet \delta I_{dc}(t) \bullet (\partial E_{10} / \partial I_{dc}) / 2 \end{aligned}$$

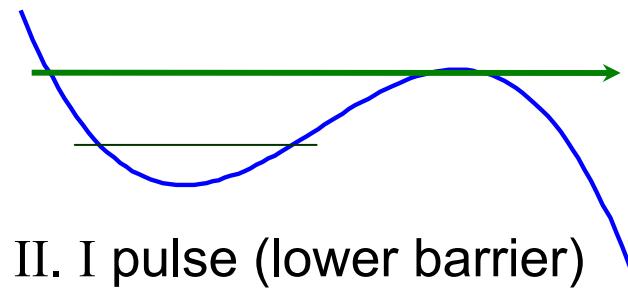
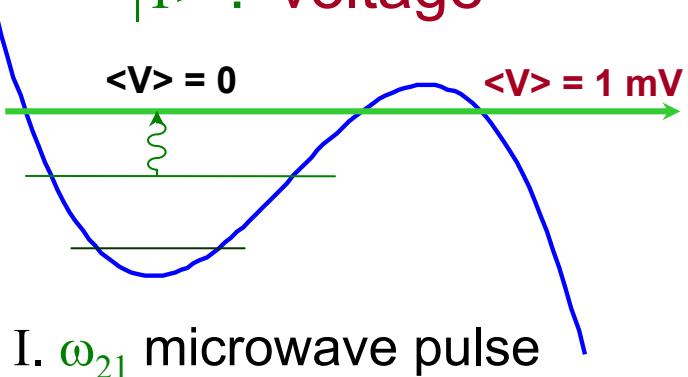
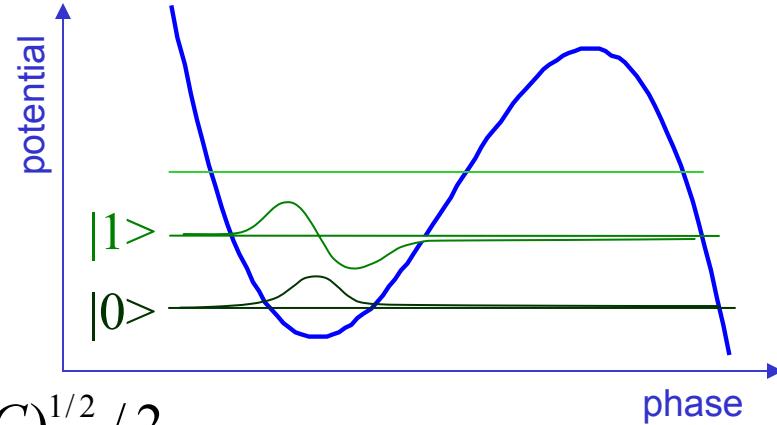
- State Measurement (Junction acts as “photomultiplier”)

$|0\rangle$: zero voltage

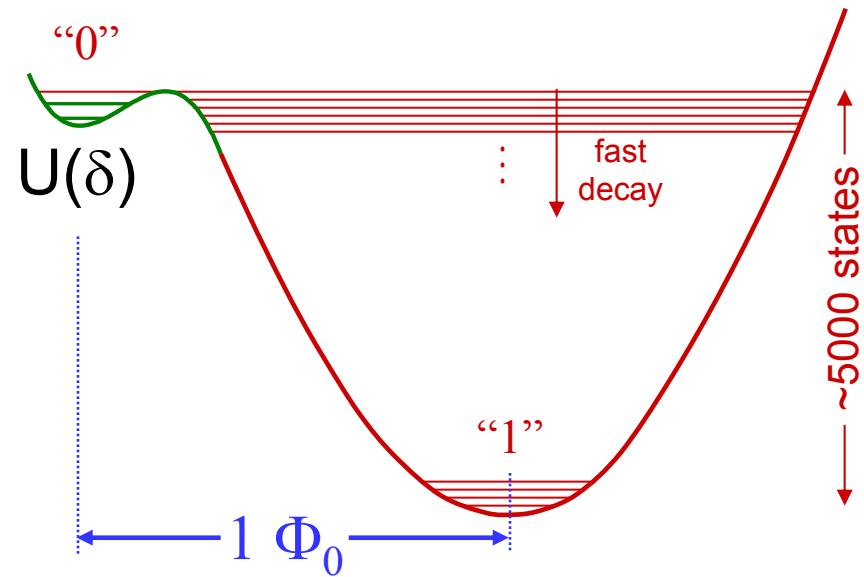
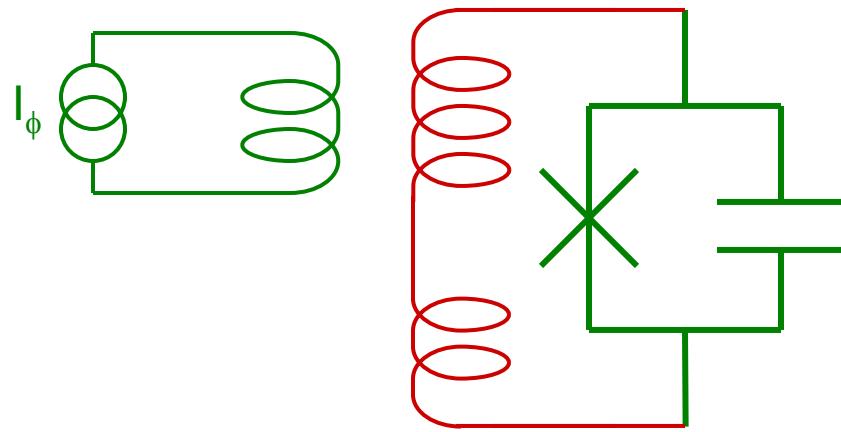
$|1\rangle$: voltage

With $\Gamma_i / \Gamma_{i-1} \sim 1000$

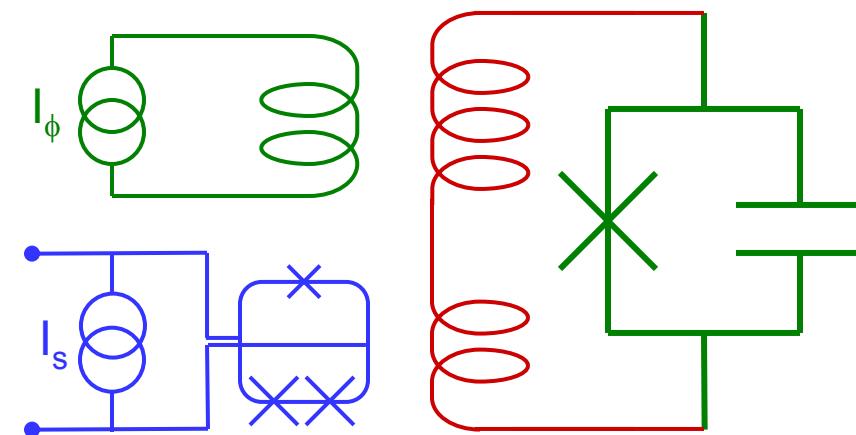
Fidelity > 99% !!



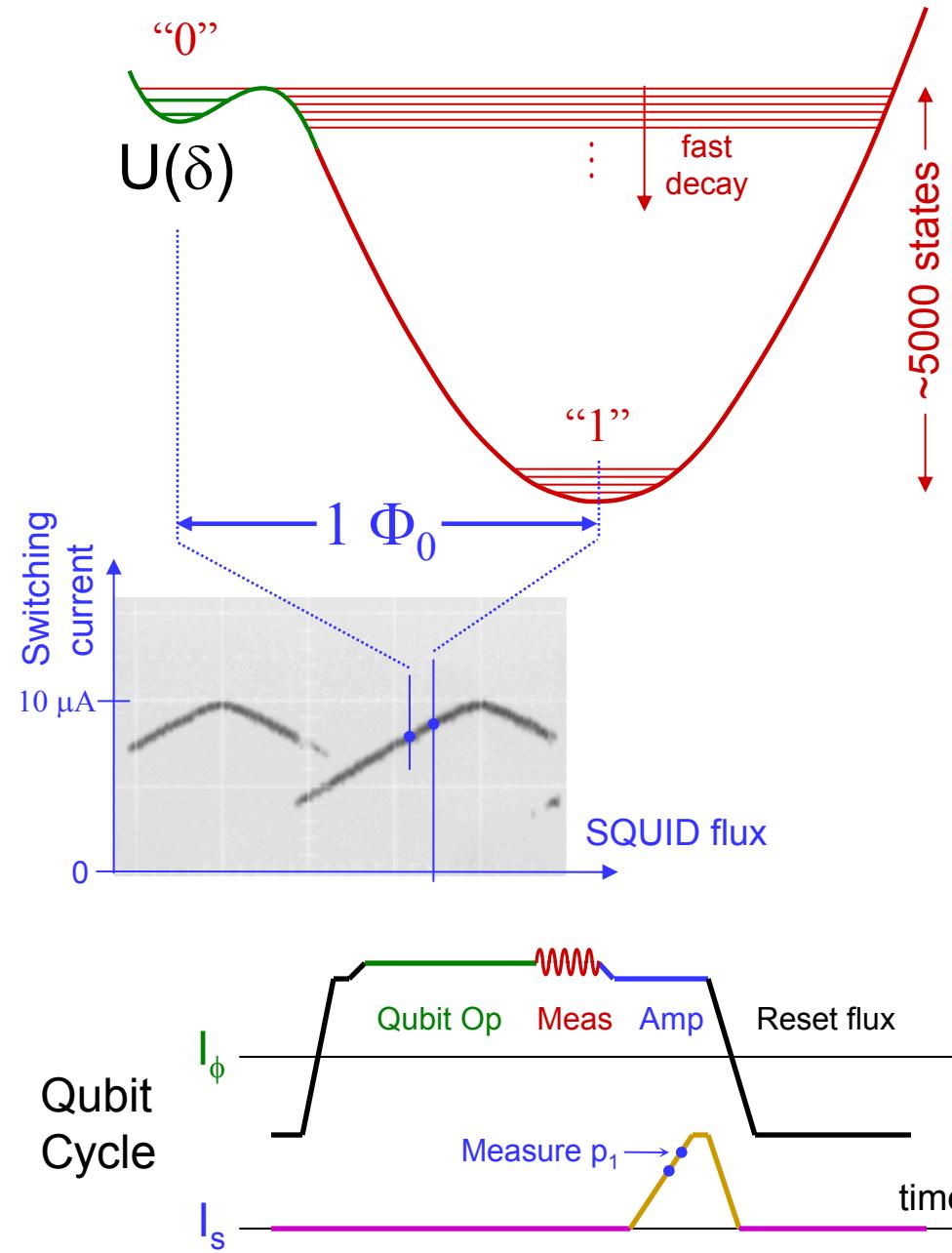
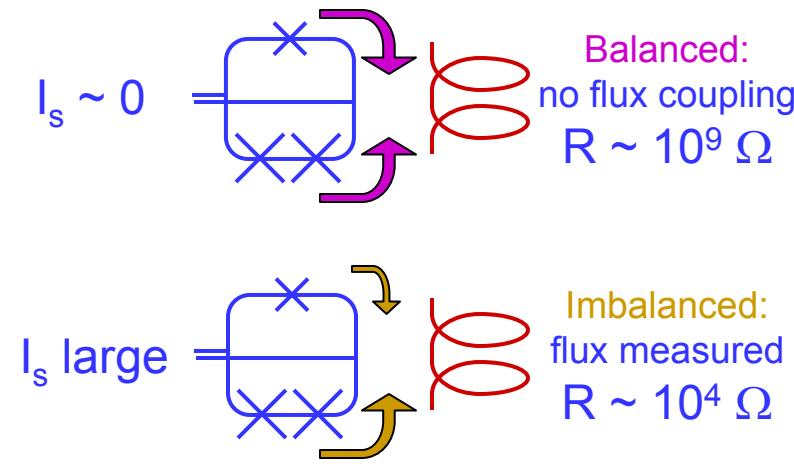
Qubit operation → Measurement



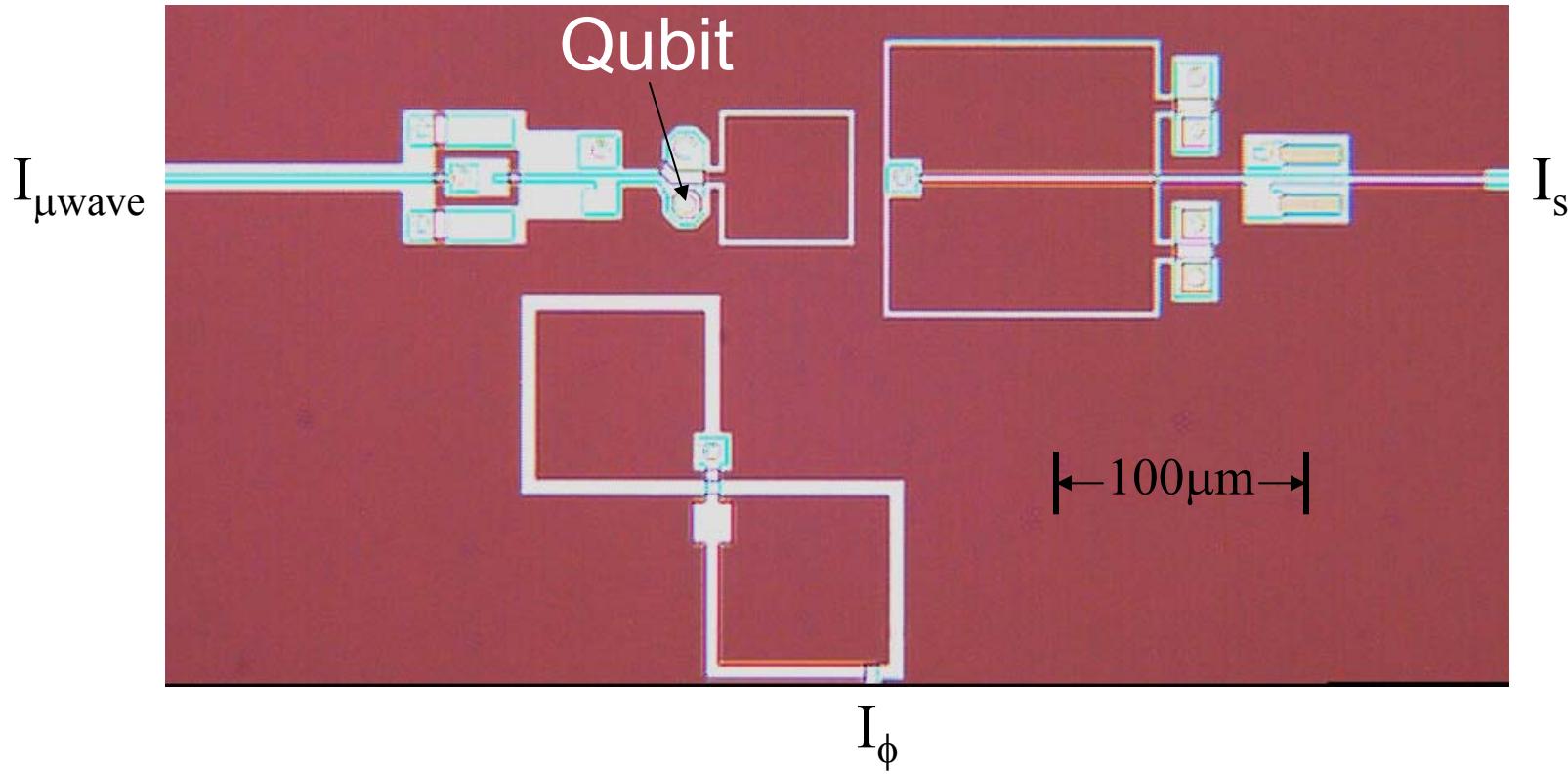
Qubit operation → Measurement → Readout



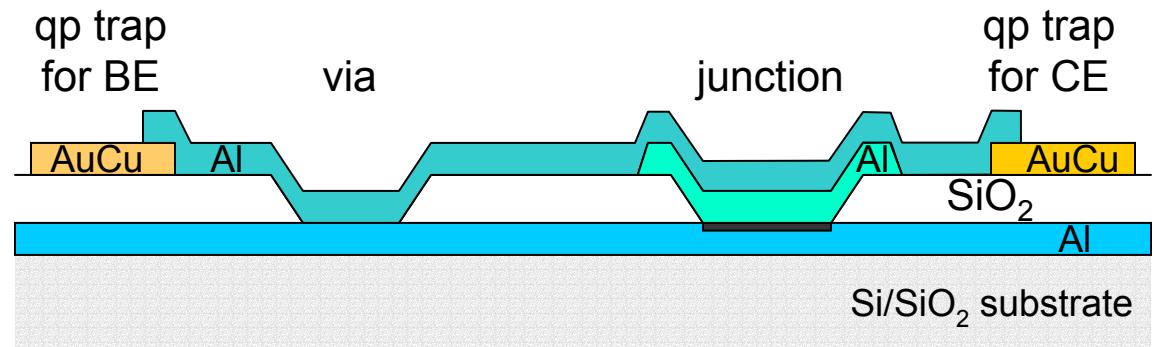
Amplifier (and its dissipation!) turned on & off with I_s
- Adjustable T_1 -

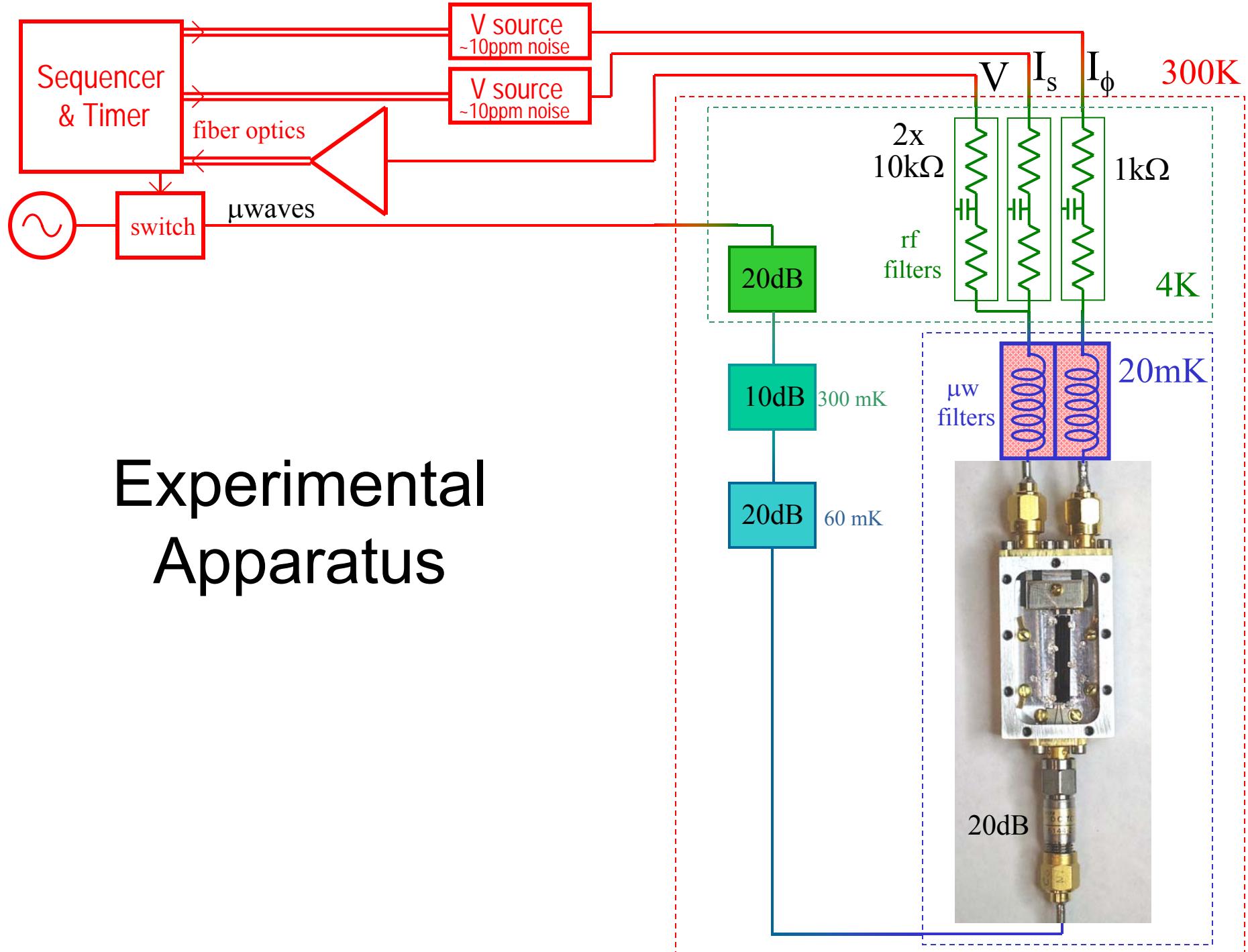


IC Fabrication

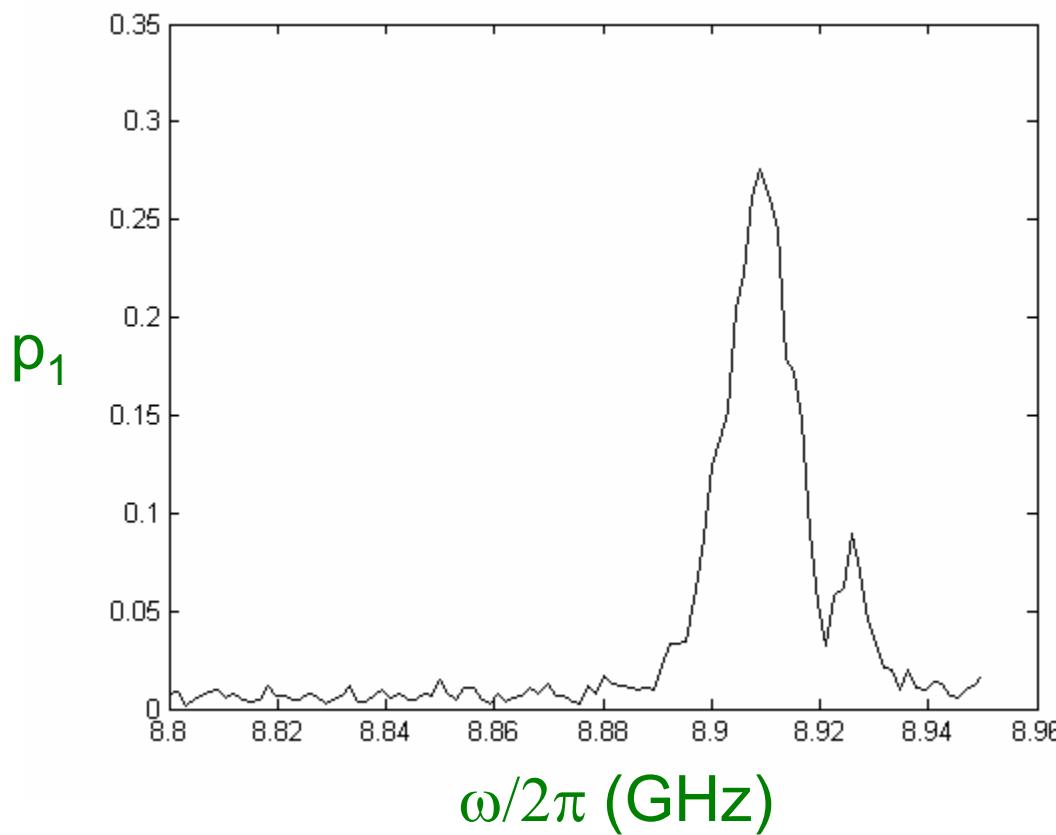
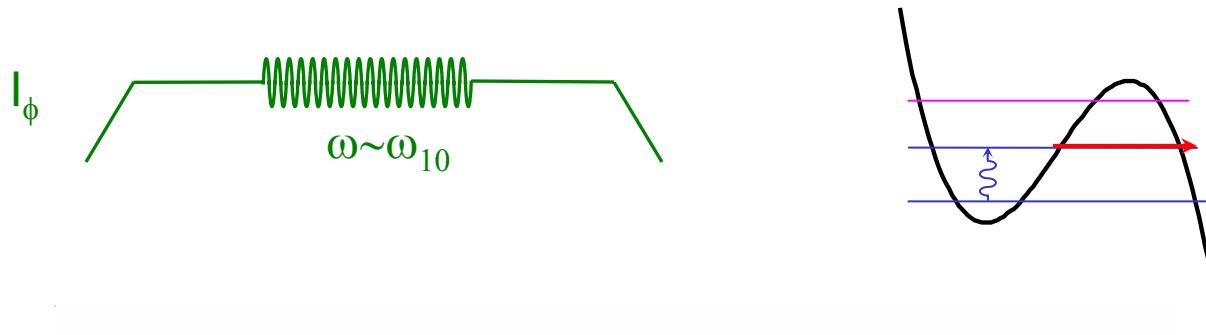


Al junction process
& optical lithography

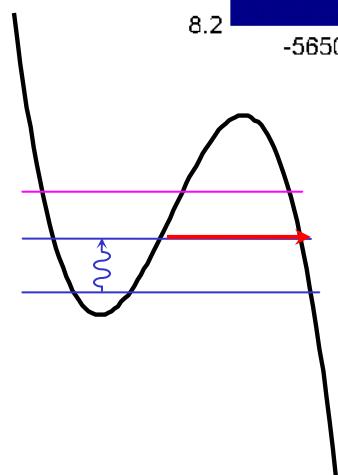
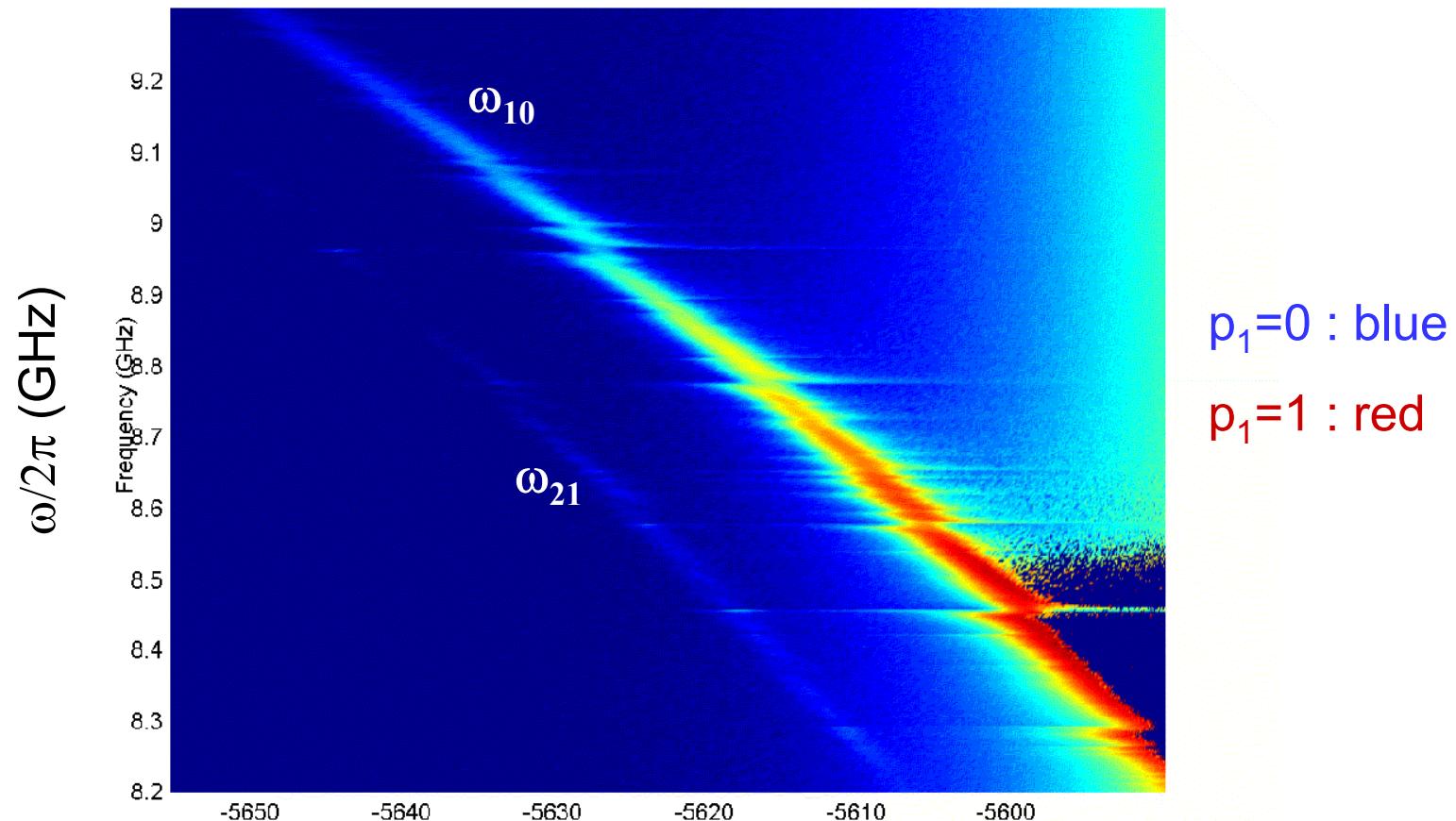




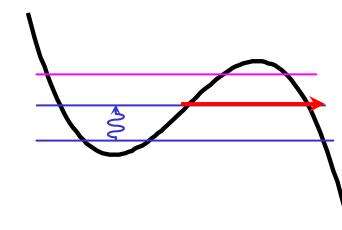
Spectroscopy



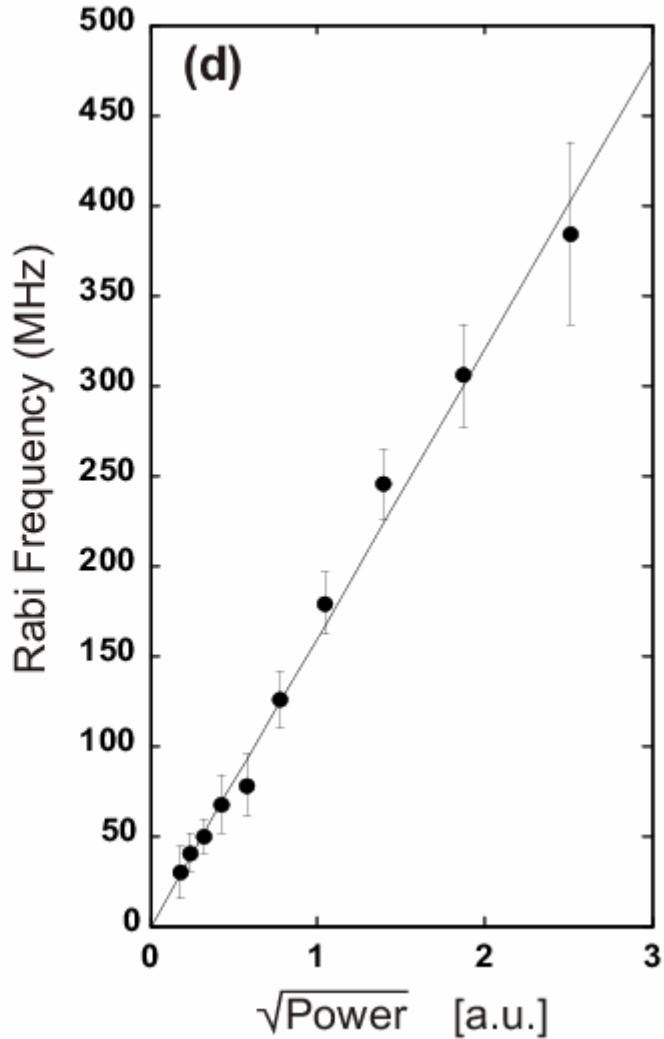
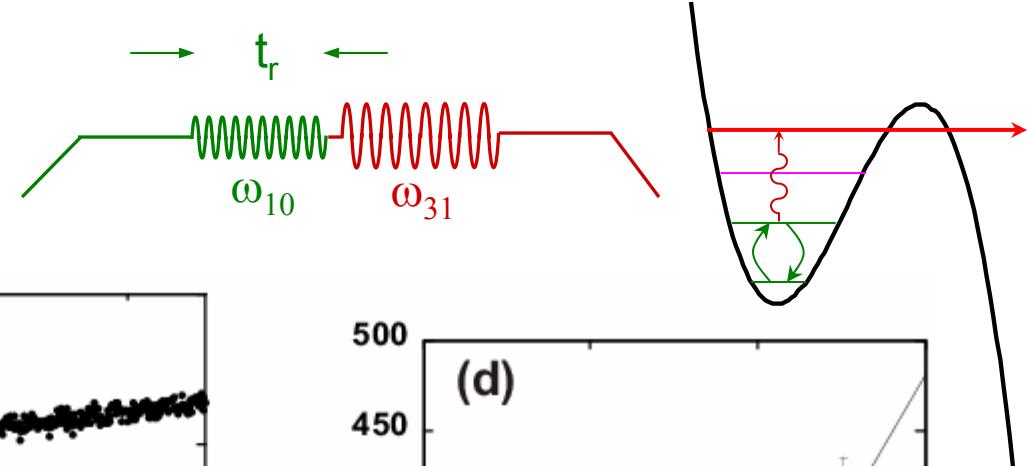
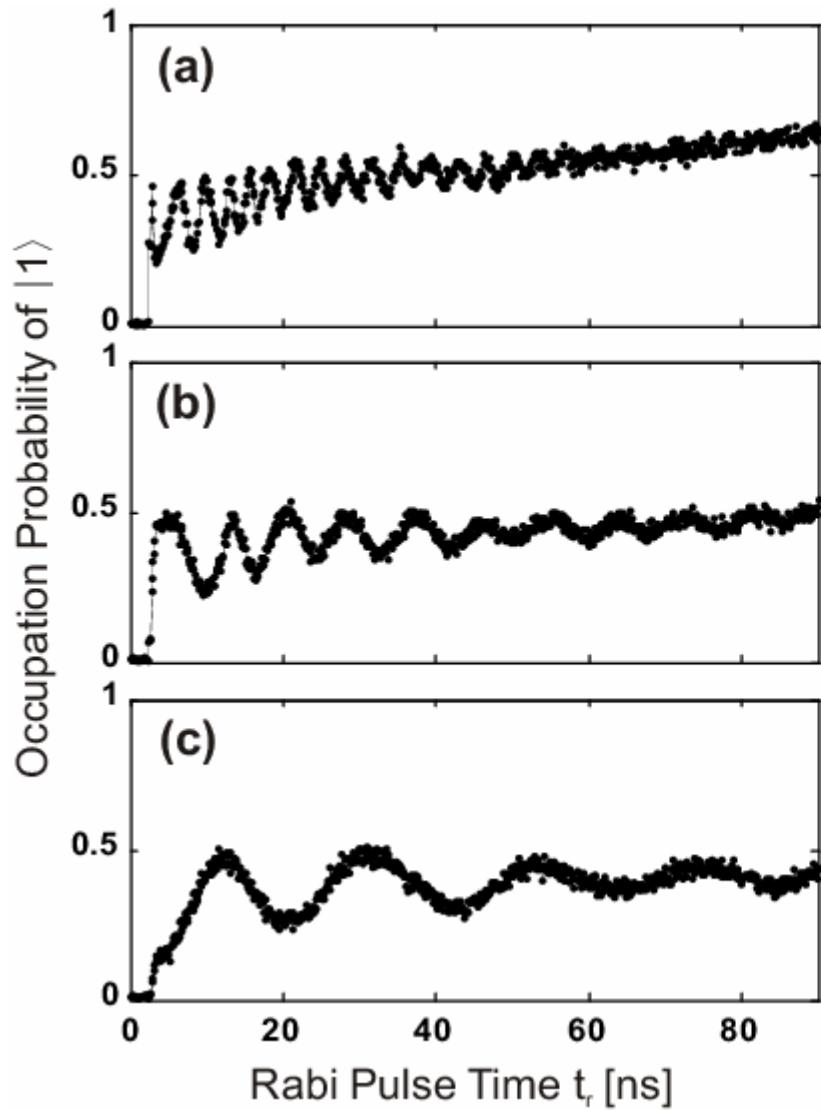
Energy Levels vs. Bias Current

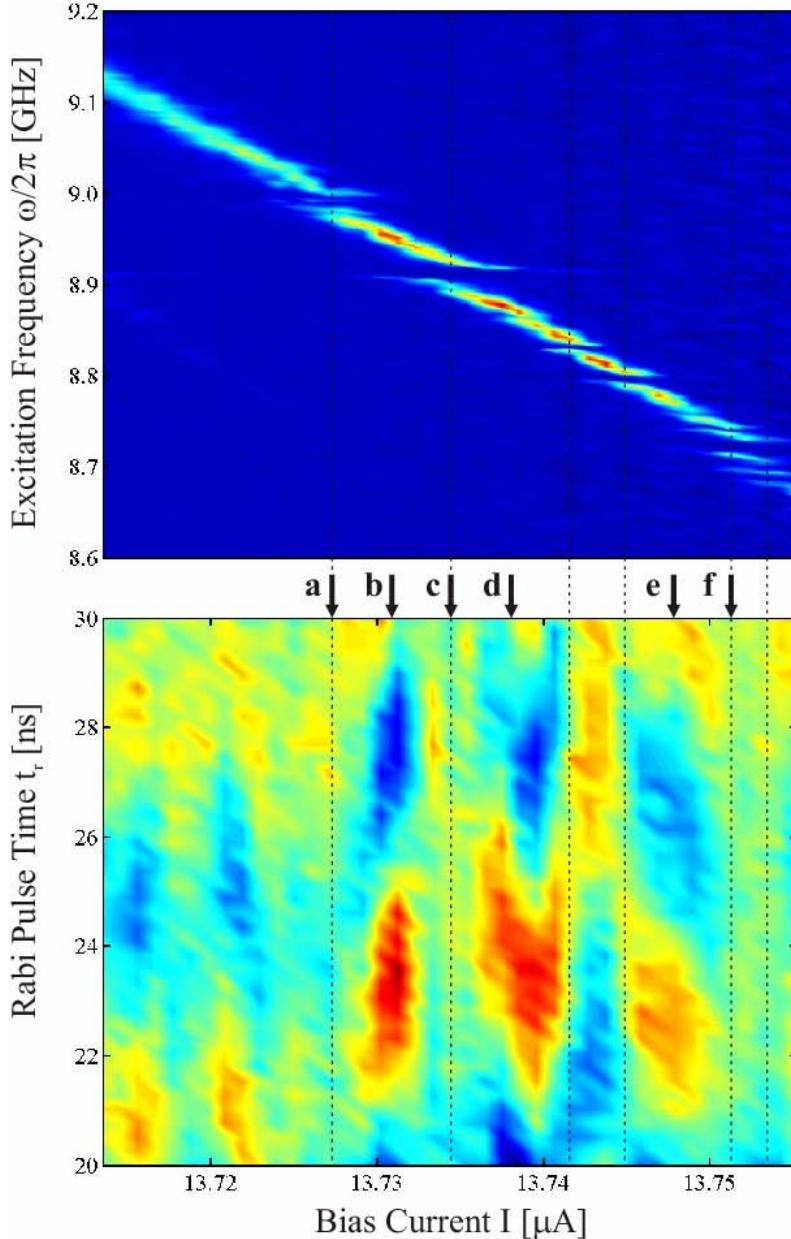


Increasing I (arb. Units)



Rabi Oscillations

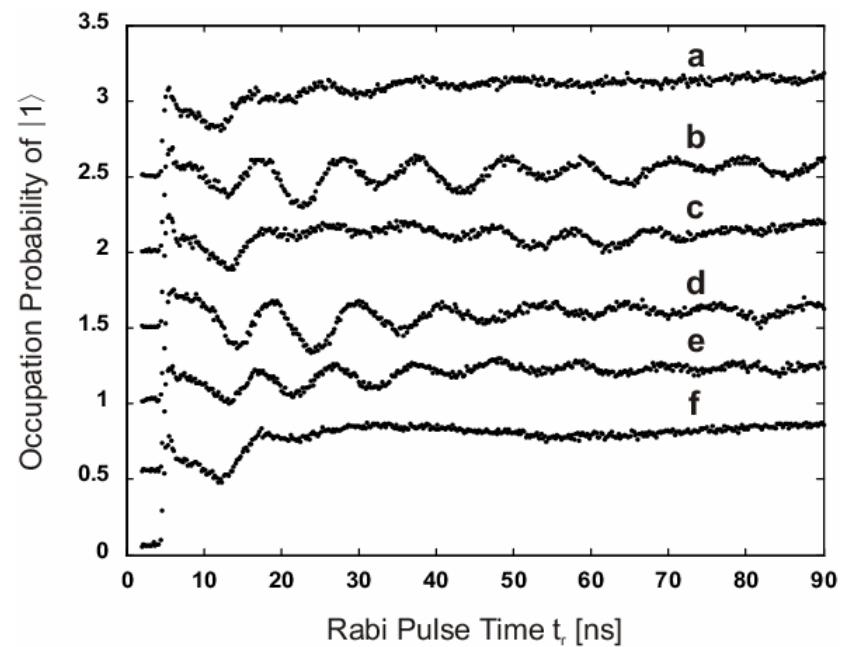




Resonances & Rabi Oscillations

$p_1=0$: blue

$p_1=1$: red



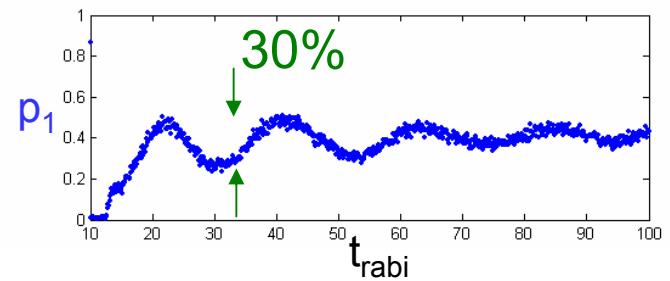
Rabi oscillations disappear
at spurious resonances

Decrease in coherence
amplitude, not coherence time

Amplitude Decoherence (Visibility)

- Need to report amplitude of oscillations

	<u>barrier</u>	<u>coh. time</u>	<u>coh. ampl.</u>
Saclay	AlOx	1 μ s	(30%)
Delft	AlOx	150 ns	50%
NIST	AlOx	41 ns	30%
NIST	NbAlOx	20 ns	15%
Kansas	AlN	5 μ s	1%



- All experiments have reduced amplitude
- Spurious resonances observed in Saclay, Delft experiments
 - Small junctions: fewer resonances, but greater effect
- Decoherence likely from many small resonances
 - All resonances reduce coherence amplitude
 - Expect and observe small resonances at optimal bias
- Resonances are major source of decoherence?!

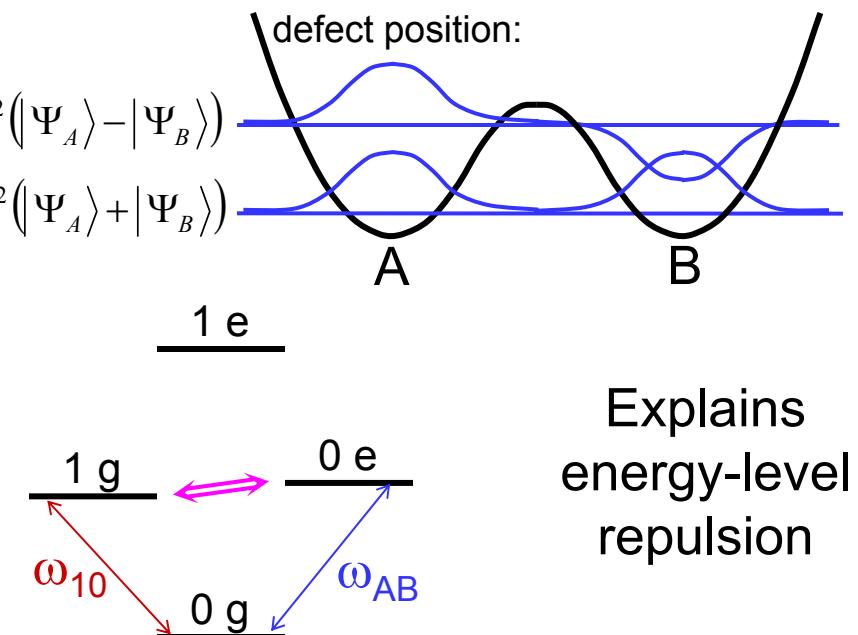
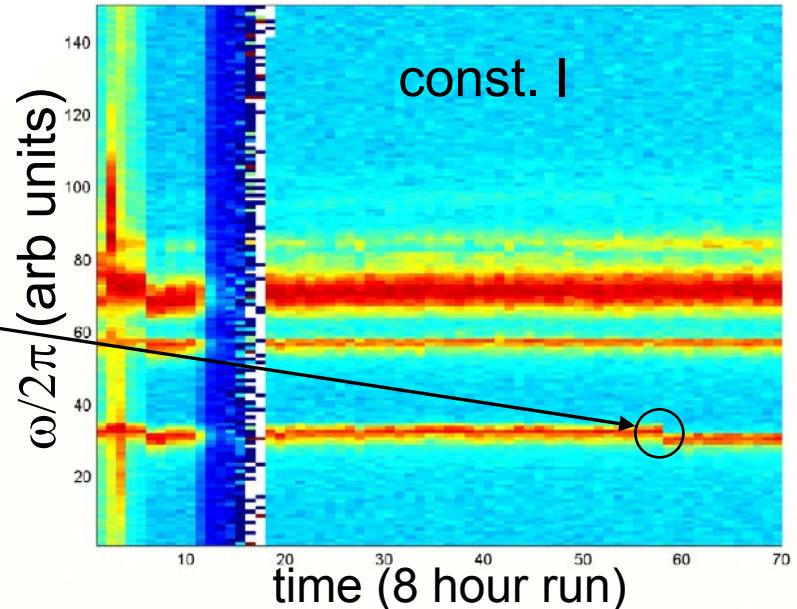
What causes extra resonances?

- Level-repulsion:
Uncontrolled “Coupled qubit”

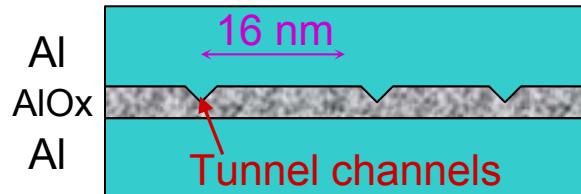
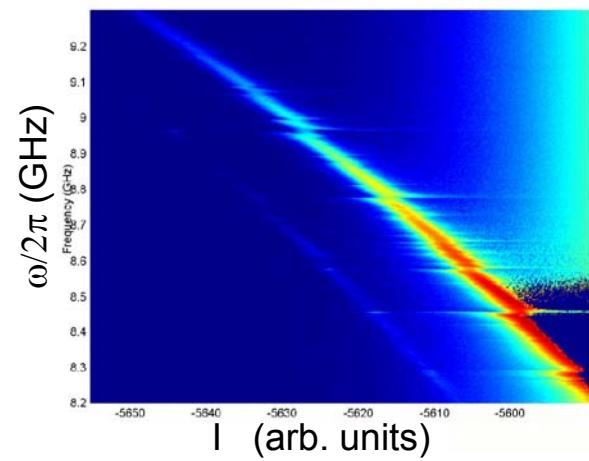
- Frequency shifts rule-out macroscopic EM modes

- Model as modulation of I_0 from resonant defect motion

$$\begin{aligned}
 H_{\text{int}} &= \left(-\frac{\Phi_0 I_{0A}}{2\pi} \cos \delta \right) \otimes |\Psi_A\rangle\langle\Psi_A| \\
 &\quad + \left(-\frac{\Phi_0 I_{0B}}{2\pi} \cos \delta \right) \otimes |\Psi_B\rangle\langle\Psi_B| \\
 &= \frac{\Delta I_0}{2} \sqrt{\frac{\eta}{2\omega_{10}C}} (|0\rangle\langle 1| \otimes |e\rangle\langle g| + |1\rangle\langle 0| \otimes |g\rangle\langle e|)
 \end{aligned}$$

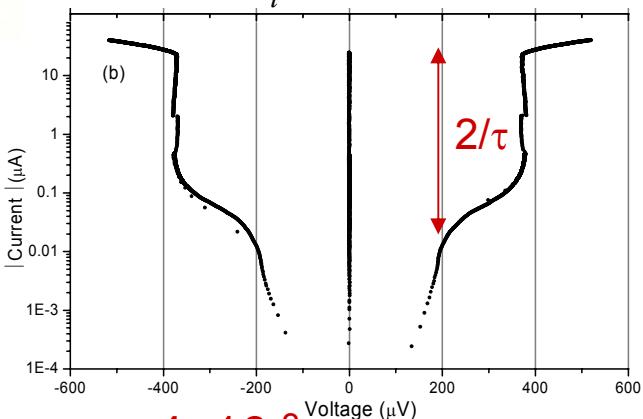


Decoherence : IV's : 1/f Noise



$$G_N = \frac{2e^2}{h} \sum_i \tau_i = \frac{2e^2}{h} N_{ch} \tau$$

$$G_{S2} \approx \frac{2e^2}{h} \sum_i \tau_i^2 \quad (\Delta < eV < 2\Delta)$$



- $\tau \sim 4 \times 10^{-3}$
- 1 channel / $(16\text{nm})^2$
- $\Delta I_0/I_0 \sim 8 \text{ ppm}$

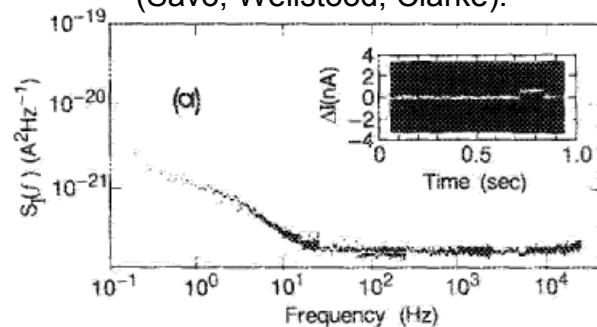


- $\Delta I_0/I_0 \sim 65 \text{ ppm}$
- 5 res. / dec.-fr. - μm^2

Assuming resonances & traps turn on/off channels:

- See individual traps in sub-micron junctions

(Savo, Wellstood, Clarke):



0.1 μm^2 junction (Van Harlingen)

- $\Delta I_0 \sim 10^{-4} I_0$
($1/N_{ch} \sim 3 \times 10^{-3}$)
- 1 trap / decade freq.

scaling to 32 μm^2

- $\Delta I_0/I_0 \sim 0.3 \text{ ppm}$
- 10 traps / dec.-fr. - μm^2

Resonances and 1/f noise are same phenomenon !

Decoherence & Materials

- All oxide tunnel barriers give similar 1/f noise

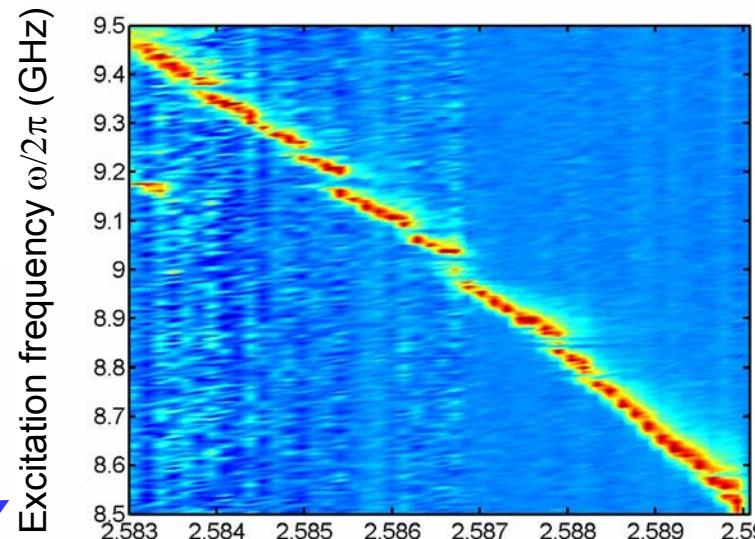
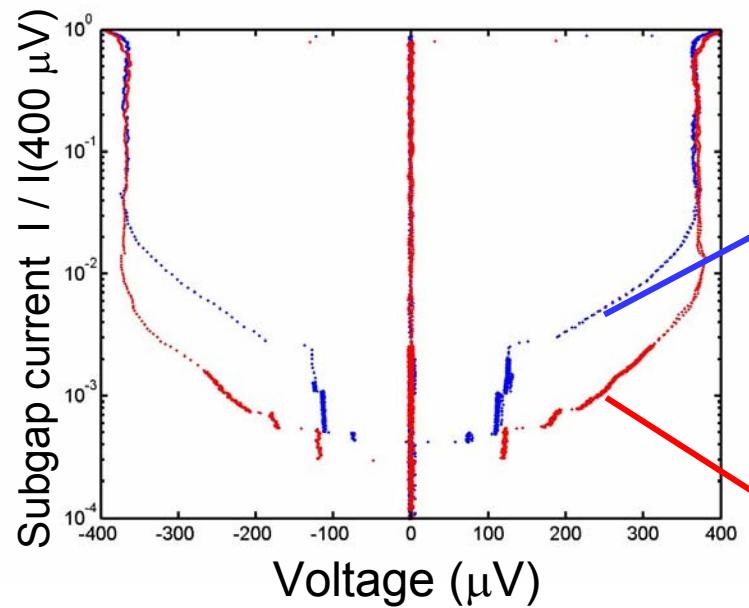
(Van Harlingen et al)	$S_{I_0}^{1/2}(1\text{Hz})A^{1/2}/I_0$ ($\mu\text{m pA}/\text{Hz}^{1/2}/\mu\text{A}$)
Al-AlOx-Al	(~5)
Nb-AlOx-Nb	7-20
Nb-Ox-PbIn	7-20
Nb-NbOx-PbInAu	8
PbIn-Ox-Pb	15
NbN-AlN-NbN (epi)	1000

- Need Materials Research – Qubits have vastly different requirements

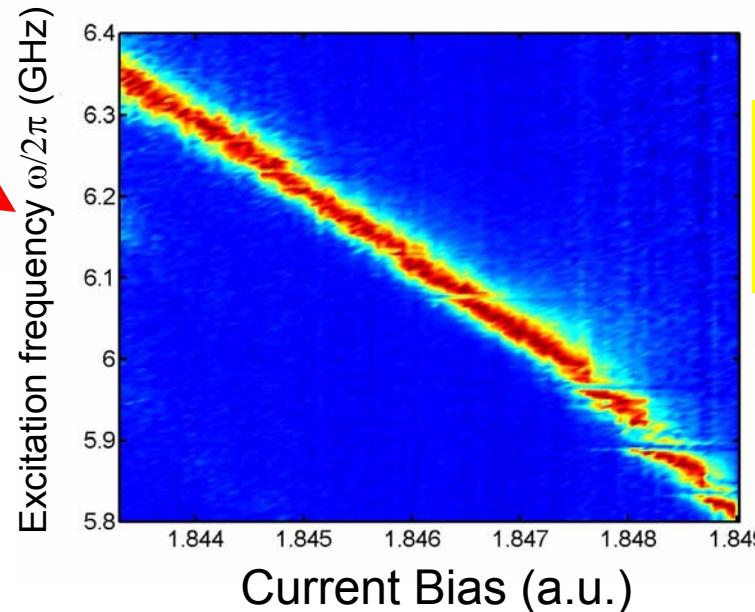
Past Research: High T_c , $Q < 1$, low leakage junctions

Qubits: $T_c > 1\text{K}$, leakage tolerated
low fluctuations, low dielectric loss

Resonance Size Correlated with Fabrication !



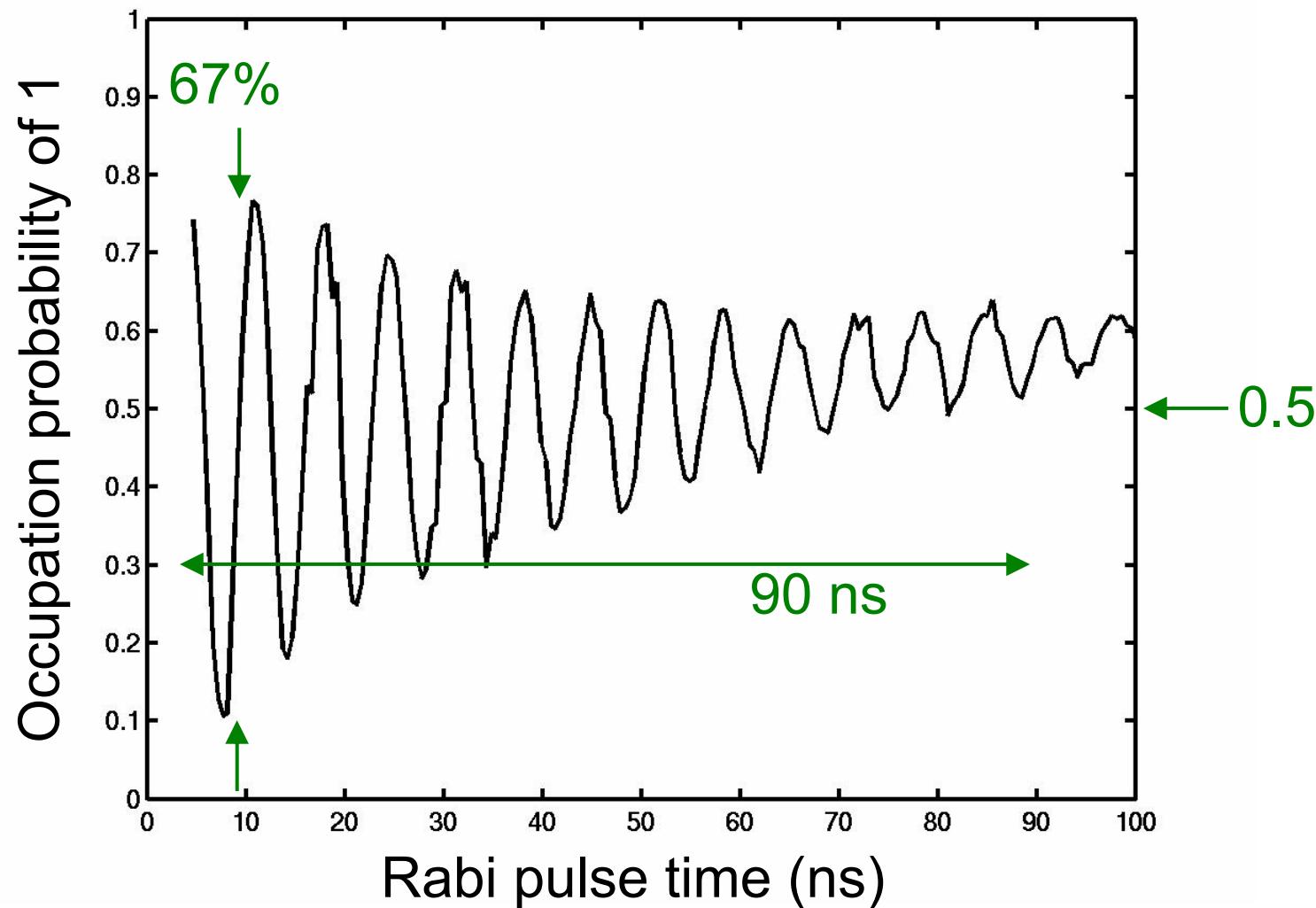
Al
Ion Mill clean
Oxidize
Al



“Clean” Fab. :
Lower subgap I
Smaller Res.

Al
Oxidize
Al

Rabi Oscillations for Trilayer Junction



Materials Research

Now have model for optimization!

- New fabrication methods for current Al-AlOx-Al devices:
 - > trilayer processing
 - > epitaxial growth of Al
 - > growth AlOx at elevated temperatures
- New substrates, junction and barrier materials:
 - > Ta as a junction material
 - > AlN barrier
 - > Al_2O_3 crystalline barrier
- For understanding & rapid optimization,
need multiple characterization tools:
 - > local probe studies- conducting atomic force microscopy and scanning tunneling microscopy
 - > Auger Electron Spectroscopy and LEED
 - > Junction IV measurements
 - > Qubit spectroscopy
 - > Coherence Time (Phase qubits ideal for testing materials)

Conjecture for All Qubits:

- Josephson qubits are insensitive to defects
- Decoherence from motion of defects
- Connected to $1/f$ noise